Device Modeling Report

COMPONENTS:THYRISTOR
PART NUMBER:MCR8DSN
MANUFACTURER: ON SEMICONDUCTOR

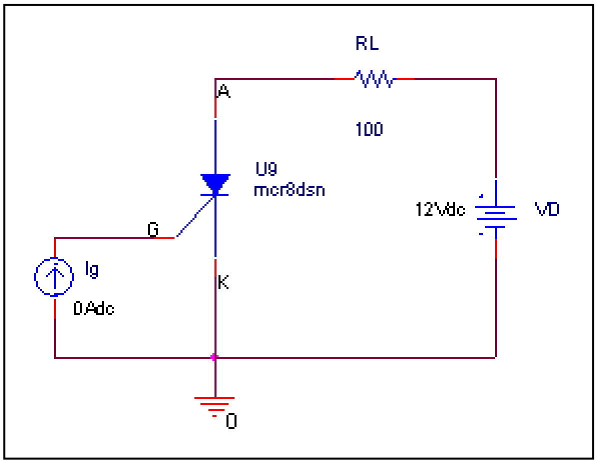
Bee Technologies Inc.

DIODE MODEL

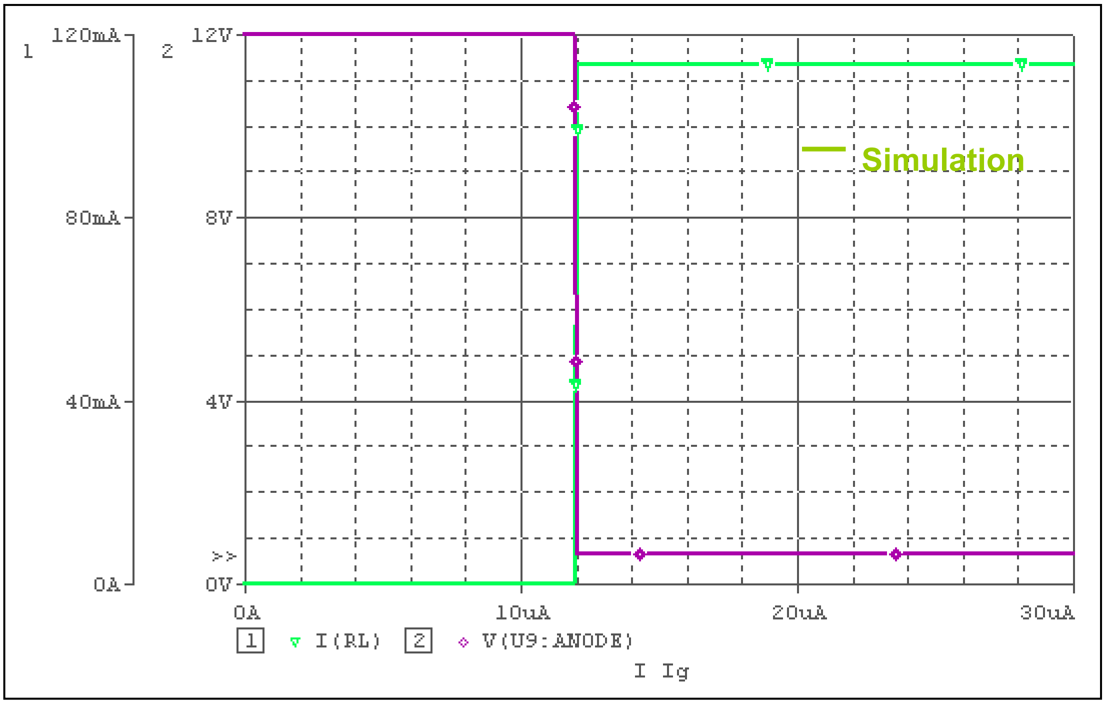
Pspice model Parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

IG-VT Characteristic

Evaluation Circuit



Simulation result

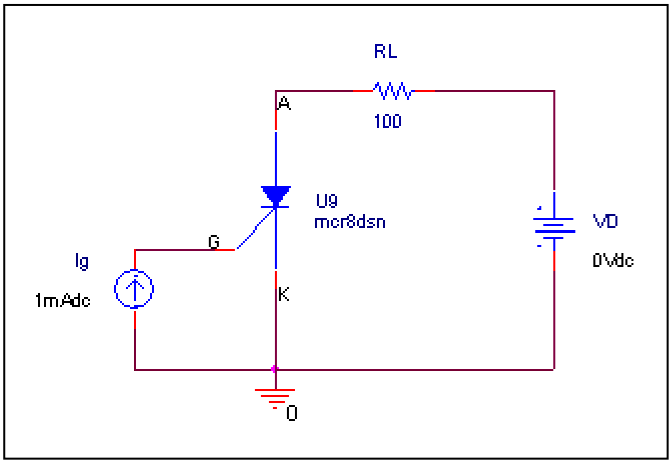


Comparison Table

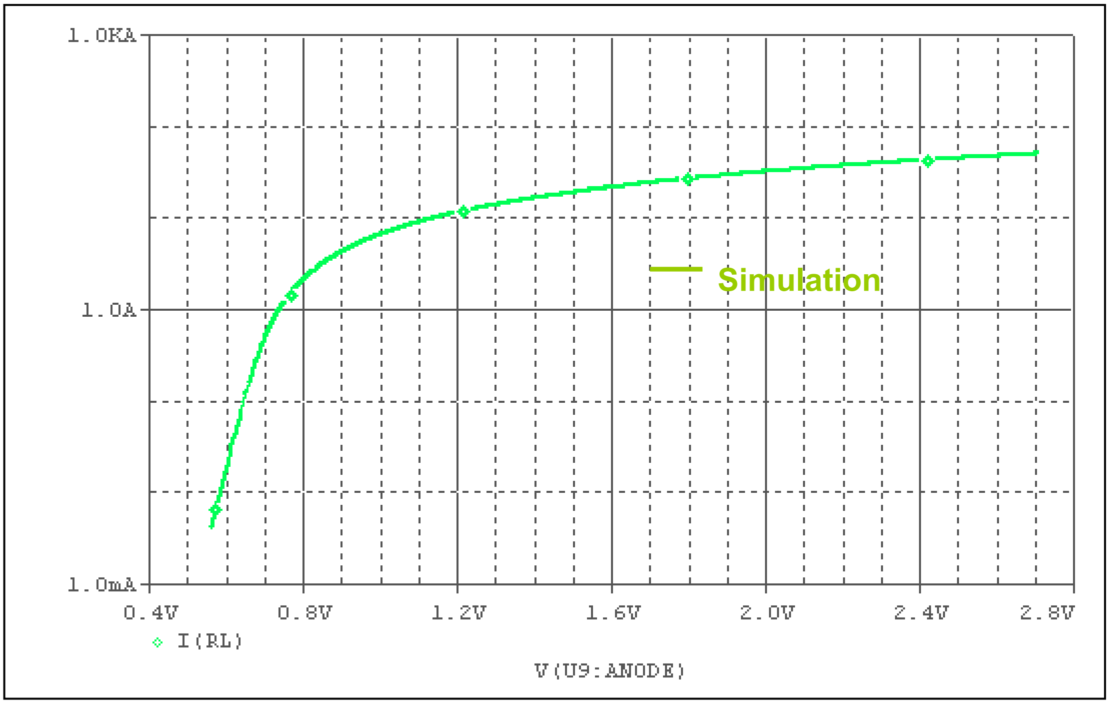
	Measurement	Simulation	% Error
IG_T (uA)	12	11.915	-0.70833
V_{GT} (V)	0.65	0.649294	-0.10862

ITM-VTM Characteristic

Evaluation Circuit



Simulation result

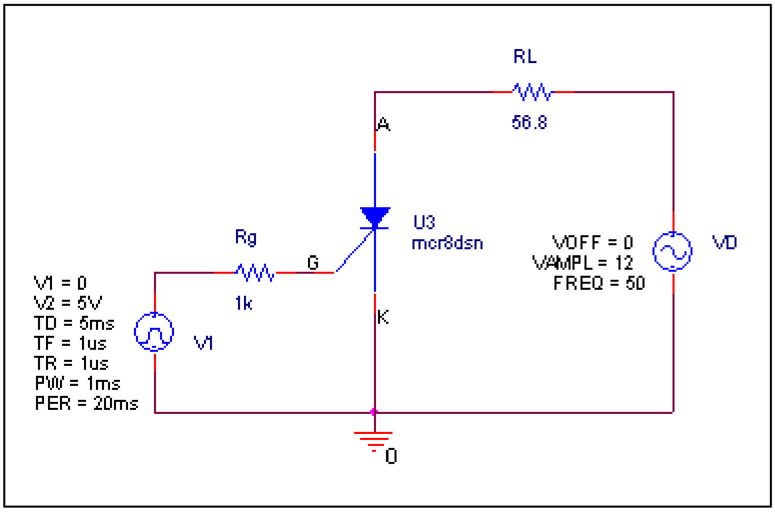


Comparison Table

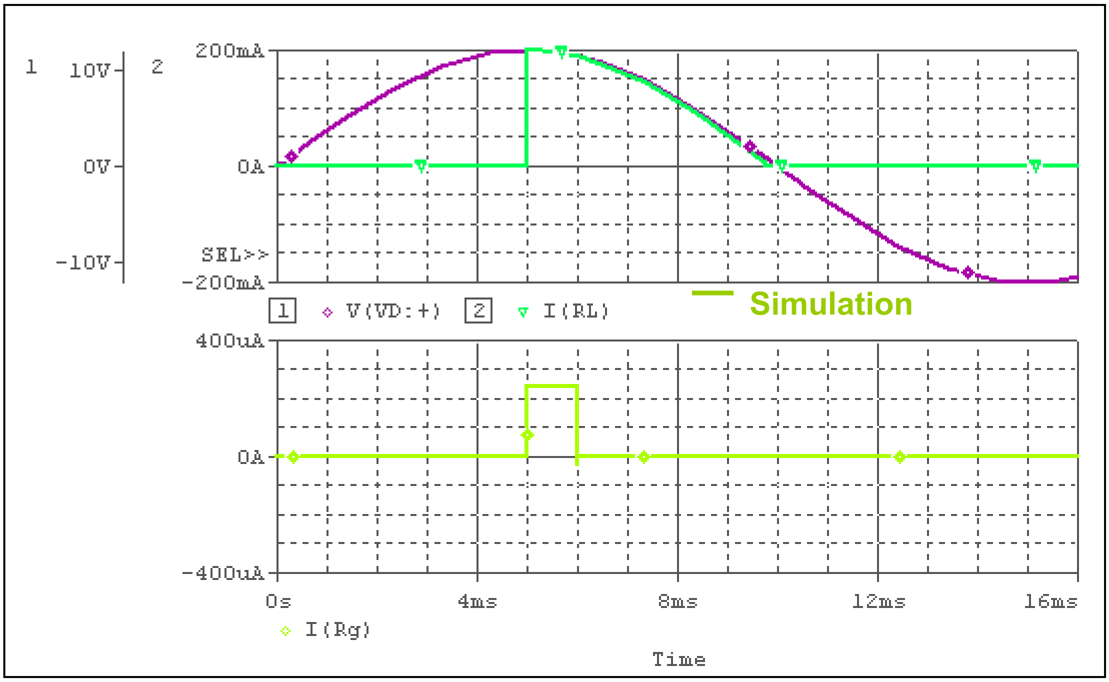
At ITM=16A	Measurement	Simulation	% Error
VTM(V)	1.4	1.3852	-1.05714

Holding Characteristic (IH)

Evaluation Circuit



Simulation result

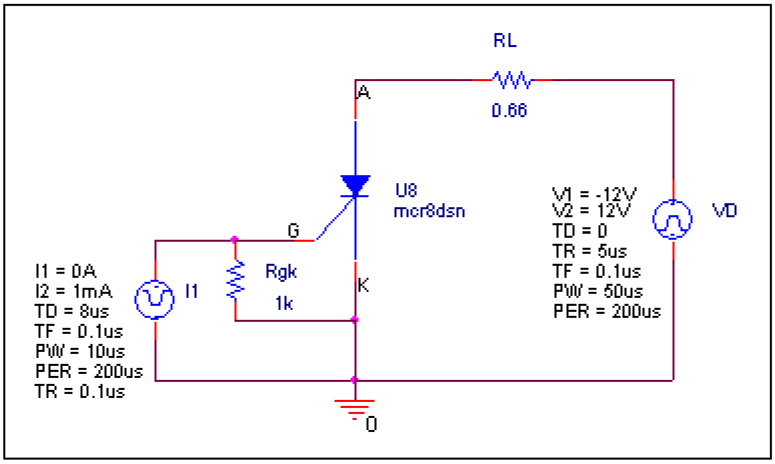


Comparison Table

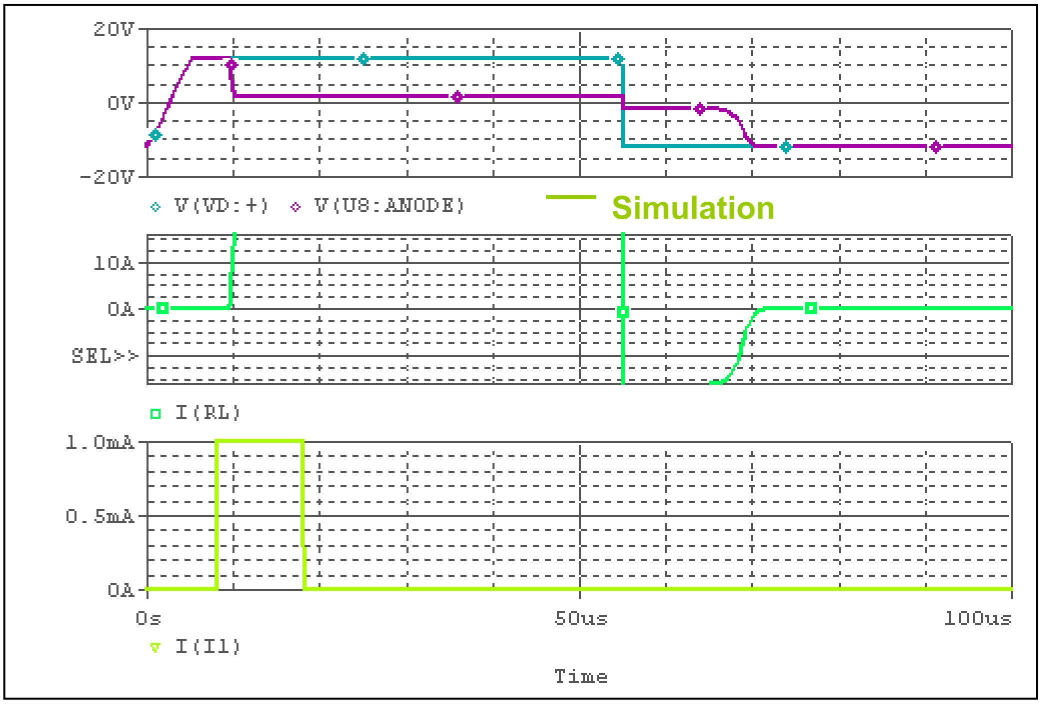
VD=12V	Measurement	Simulation	% Error
IH(mA)	6.0(max)	5.8354	-2.74333

Switching Time Characteristic

Evaluation Circuit



Simulation result



Comparison Table

	Measurement	Simulation	%Error
Ton(us)	**2.0**	**1.9834**	**-0.8300**